

MS1008

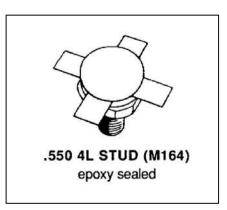
RF & MICROWAVE TRANSISTORS HF SSB APPLICATIONS

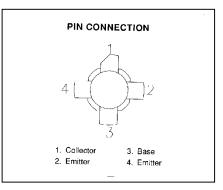
Features

- 30 MHz
- 50 VOLTS
- IMD = -30 dB
- **P**_{OUT} = 150 WATTS
- $G_P = 14 \text{ dB MINIMUM}$
- COMMON EMITTER CONFIGURATION



The MS1008 is a 50V epitaxial silicon NPN planar transistor designed primarily for SSB communications. This device utilizes emitter ballasting to achieve extreme ruggedness under severe operating conditions.





ABSOLUTE MAXIMUM RATINGS (Tcase = 25°C)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	110	V
V _{CEO}	Collector-Emitter Voltage	55	V
V _{EBO}	Emitter-Base Voltage	4.0	V
Ιc	Device Current	10	Α
PDISS	Power Dissipation	233	W
TJ	Junction Temperature	+200	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Thermal Data

R _{TH(J-C)} Junction-Case Thermal Resistance	0.75	°C/W
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Rev A 11/2005



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ELECTRICAL SPECIFICATIONS (Tcase = 25° C)

STATIC

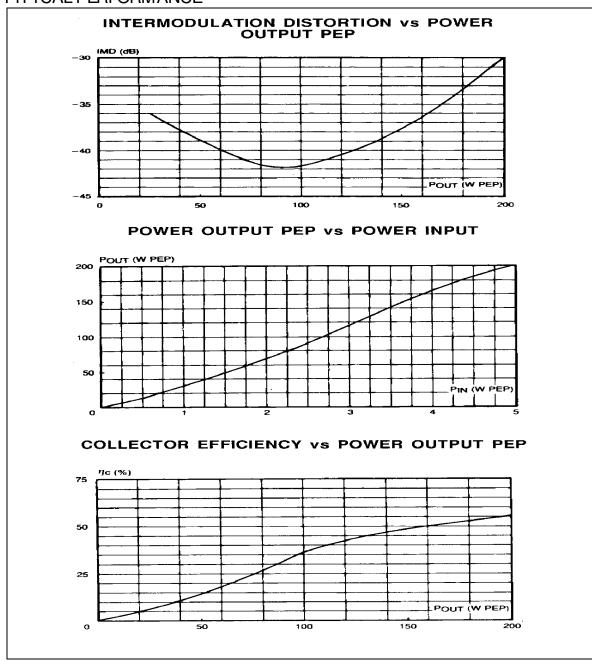
Symbol	Test Conditions		Value			
	rest conditions		Min.	Typ.	Max.	Unit
BV _{CBO}	I _c = 100mA	l _E = 0mA	110			V
BV _{CES}	I _c = 100mA	$V_{BE} = 0V$	110			V
BV _{CEO}	I _c = 100mA	I _в = 0mА	55			V
BV EBO	I _E = 10mA	I _c = 0mA	4.0			V
I _{CEO}	V _{CE} = 30V	l _E = 0 mA			5	mA
I _{CES}	V _{CE} = 60V	I _E = 0mA			5	mA
h _{FE}	$V_{CE} = 6V$	I _C = 1.4A	15		50	
h _{FE,,} MS1008A	$V_{CE} = 6V$	I _C = 1.4A	20		30	

DYNAMIC

Symbol	Test Conditions			Value			
Symbol			Min.	. Typ. Max.	Max.	Unit	
Pout	f = 30 MHz	$V_{CE} = 50V$	I _{CQ} = 150mA	150			WPEP
G _P	P _{OUT} = 150WPEP	V _{CE} = 50V	I _{CQ} = 150mA	14			dB
IMD	P _{OUT} = 150WPEP	V _{CE} = 50V	I _{CQ} = 150mA			-30	dBc
ηc	P _{OUT} = 150WPEP	V _{CE} = 50V	I _{CQ} = 150mA	37			%
Сов	f = 1 MHz	V _{CB} = 50 V				220	pF
Conditions:	f ₁ = 30.000MH	$z f_2 = 30.0$	01MHz	•			·



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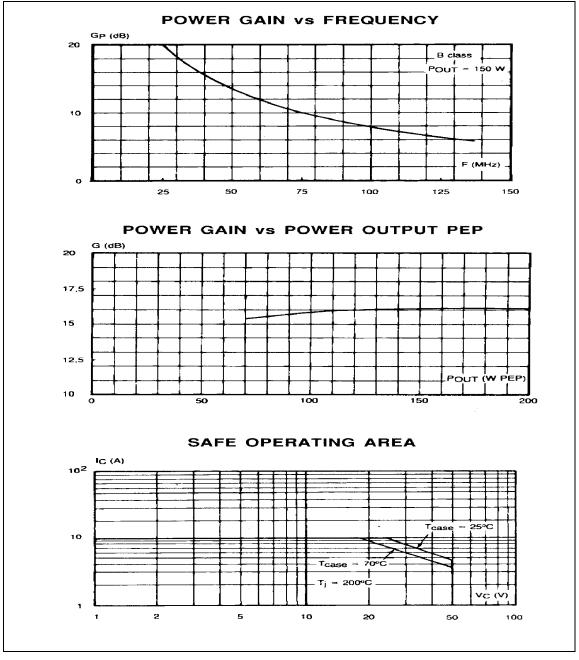


TYPICAL PERFORMANCE



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TYPICAL PERFORMANCE





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PACKAGE MECHANICAL DATA

